

Medium Power Transistor (—80V, —0.7A)

2SB1189 / 2SB1238 / 2SB889F

●Features

- 1) High breakdown voltage, $BV_{CEO} = -80V$, and high current, $-0.7A$.
- 2) Complements the 2SD1767 / 2SD1859 / 2SD1200F.

●Packaging specifications and hrc

Type	2SB1189	2SB1238	2SB889F
Package	MPT3	ATV	TO-126FP
hrc	PQR	PQR	Q
Marking	BD*	—	—
Code	T100	TV2	—
Basic ordering unit (pieces)	1000	2500	1000

* Denotes hrc

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit		
Collector-base voltage	V_{CBO}	-80	V		
Collector-emitter voltage	V_{CEO}	-80	V		
Emitter-base voltage	V_{EBO}	-5	V		
Collector current	I_C	-0.7	A		
Collector power dissipation	2SB1189 2SB1238 2SB889F	Pc	0.5	W *1	
			2		*2
			5		
Junction temperature	T_J	150	°C		
Storage temperature	T_{stg}	-55~+150	°C		

*1 When mounted on a 40×40×0.7mm ceramic board.

*2 Printed circuit board 1.7mm thick, collector plating 1cm² or larger.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	
Collector-base breakdown voltage	BV_{CBO}	-80	—	—	V	$I_C = -50 \mu A$	
Collector-emitter breakdown voltage	BV_{CEO}	-80	—	—	V	$I_C = -2mA$	
Emitter-base breakdown voltage	BV_{EBO}	-5	—	—	V	$I_C = -50 \mu A$	
Collector cutoff current	I_{CO}	—	—	-0.5	μA	$V_{CE} = -50V$	
Emitter cutoff current	I_{EO}	—	—	-0.5	μA	$V_{ES} = -4V$	
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	-0.2	-0.4	V	$I_C/I_E = -500mA/-50mA$	
DC current transfer ratio	2SB1189, 2SB1186A 2SB889F	h _{FE}	82	—	390	—	$V_{CE}/I_C = -3V/-0.1A$
			120	—	270	—	
Transition frequency	f_T	—	100	—	MHz	$V_{CE} = -10V, I_C = 50mA, f = 100MHz$	
Output capacitance	C_{ob}	—	14	20	pF	$V_{CE} = -10V, I_C = 0A, f = 1MHz$	

(96-618-B13)

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●Features

- 1) High breakdown voltage, $BV_{CEO} = 80V$, and high current, $0.7A$.
- 2) Complements the 2SB1189 / 2SB1238 / 2SB889F.

●Packaging specifications and hrc

Type	2SD1767	2SD1859	2SD1200F
Package	MPT3	ATV	TO-126FP
hrc	PQR	QR	QR
Marking	DC*	—	—
Code	T100	TV2	—
Basic ordering unit (pieces)	1000	2500	1000

* Denotes hrc

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit		
Collector-base voltage	V_{CBO}	80	V		
Collector-emitter voltage	V_{CEO}	80	V		
Emitter-base voltage	V_{EBO}	5	V		
Collector current	I_C	0.7	A (DC)		
		1	A (Pulse) *1		
Collector power dissipation	2SD1767 2SD1859 2SD1200F	Pc	0.5	W *2	
			2		*3
			5		
Junction temperature	T_J	150	°C		
Storage temperature	T_{stg}	-55~+150	°C		

*1 $P_w = 10ms, duty = 1/2$

*2 When mounted on a 40×40×0.7mm ceramic board.

*3 Printed circuit board 1.7mm thick, collector plating 1cm² or larger.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	
Collector-base breakdown voltage	BV_{CBO}	80	—	—	V	$I_C = 50 \mu A$	
Collector-emitter breakdown voltage	BV_{CEO}	80	—	—	V	$I_C = 2mA$	
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_C = 50 \mu A$	
Collector cutoff current	I_{CO}	—	—	0.5	μA	$V_{CE} = 50V$	
Emitter cutoff current	I_{EO}	—	—	0.5	μA	$V_{ES} = 4V$	
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.2	0.4	V	$I_C/I_E = 500mA/50mA$	
DC current transfer ratio	2SD1767 2SD1859, 2SD1200F	h _{FE}	82	—	390	—	$V_{CE}/I_C = 3V/0.1A$
			120	—	390	—	
Transition frequency	f_T	—	120	—	MHz	$V_{CE} = 10V, I_C = 50mA, f = 100MHz$	
Output capacitance	C_{ob}	—	10	—	pF	$V_{CE} = 10V, I_C = 0A, f = 1MHz$	

(96-750-D13)

